

INTERLEVEL DIELECTRIC LAYER AND METAL LAYER SEALING

Abstract

Methods for sealing an organic ILD layer and a metal layer after an etching step. The method includes etching through an ILD layer and leaving a remaining portion of an underlying metal layer cap, maintaining the device in an inert gas, and depositing at least a portion of a liner into the opening to seal the ILD layer and the metal layer. Subsequent processing may include formation of a via by etching through the portion of the liner and the remaining portion of the cap layer, and depositing a metal.